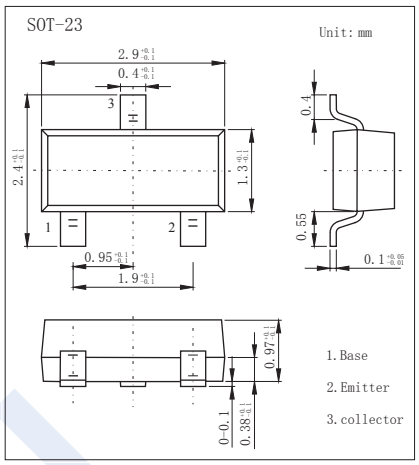
PNP Transistors

2SB1295



■ Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Complimentary to 2SD1935.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-15	V
Collector - Emitter Voltage	V_{CEO}	-15	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-0.8	A
Collector Current - Pulse	I_{CP}	-3	A
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-15			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, R_{BE}=∞	-15			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= - 12V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-5 mA, I_B=-0.5mA		-10	-25	mV
		I_C=-400 mA, I_B=-20mA		-100	-200	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-400 mA, I_B=-20mA		-0.9	-1.2	V
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -50mA	135		600	
		V_{CE}= -2V, I_C= -800mA	80			
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz		15		pF
Transition frequency	f_T	V_{CE}= -2V, I_E= 50mA		300		MHz

■ Classification of $h_{fe(1)}$

Type	2SB1295-UL5	2SB1295-UL6	2SB1295-UL7
Range	135-270	200-400	300-600
Marking	UL5	UL6	UL7

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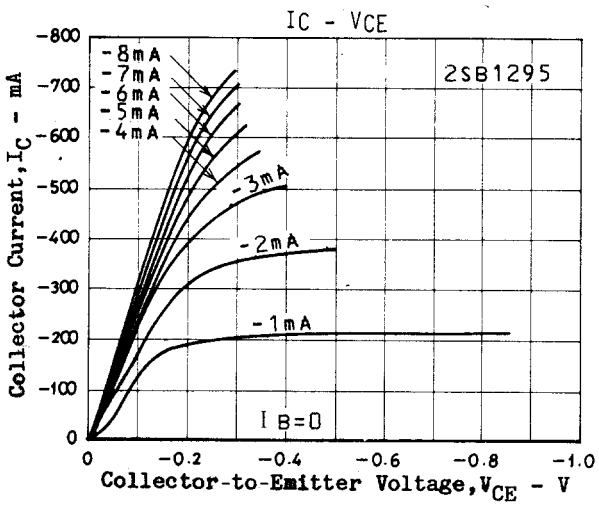
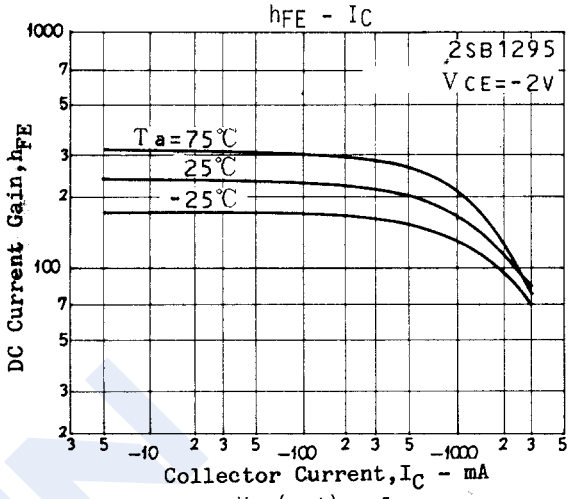
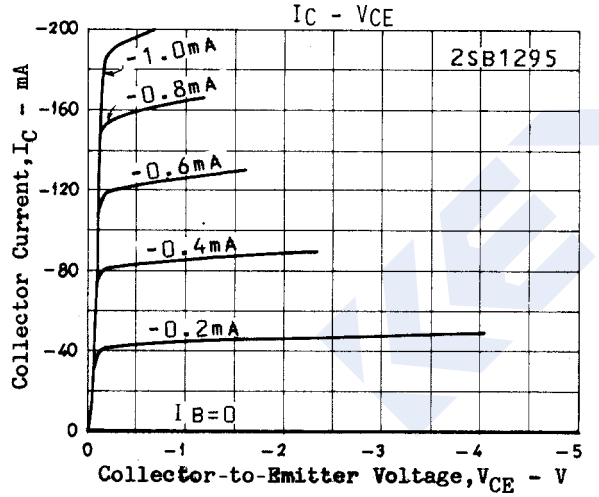
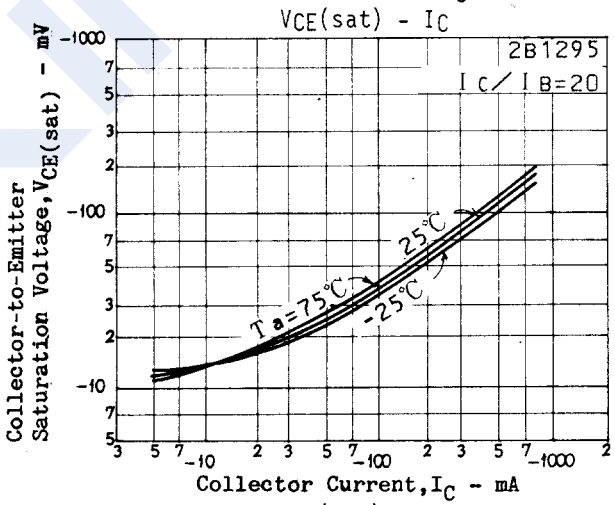
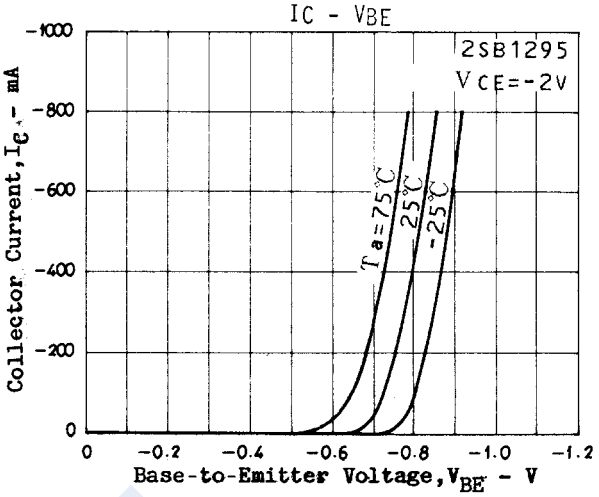
■ Typical Characterisitics

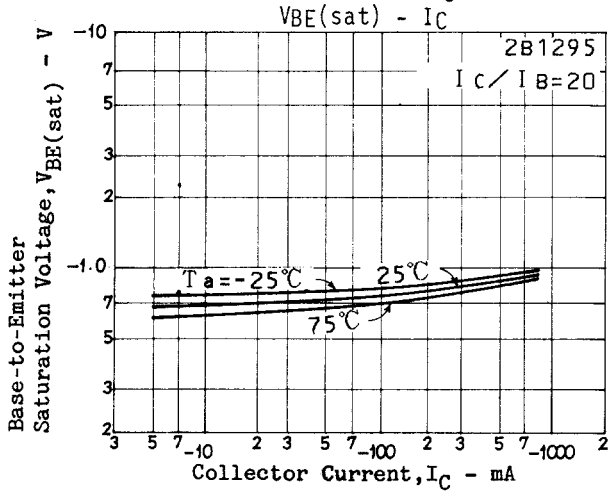












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■ Typical Characterisitics